L Number	Hits	Search Text	DB	Time stamp
151	6	(different adj material).clm. and (gate adj	USPAT;	2004/11/08
		wiring).clm.	US-PGPUB;	14:47
, [EPO; JPO;	
·			DERWENT;	
			IBM_TDB	
152	5	(different adj material).clm. and (gate adj	USPAT;	2004/11/08
		wiring).clm. and (gate adj electrode).clm.	US-PGPUB;	14:50
•			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
153	1	(different adj material).clm. and (gate adj	USPAT;	2004/11/08
	_	wiring).clm. and (gate adj electrode).clm.	US-PGPUB;	14:49
		and channel.clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
154	44	(different).clm. and (gate adj wiring).clm.	USPAT;	2004/11/08
		and (gate adj electrode).clm.	US-PGPUB;	14:50
		and face and electionelique	EPO; JPO;	17.50
			DERWENT;	
			IBM_TDB	
155	15	(different).clm. and (gate adj wiring).clm.	USPAT;	2004/11/08
155	15	and (gate adj electrode).clm. and	US-PGPUB;	14:50
		channel.cim.	1	14:50
		Chamiel.Cini.	EPO; JPO;	
			DERWENT;	
156	10	((alastrada ar wiring ar asudustina ar	IBM_TDB	2004/44/09
136	. 10	((electrode or wiring or conductive or	USPAT;	2004/11/08
		conducting or metal) near10	US-PGPUB;	14:53
		(different)).clm. and (gate adj wiring).clm.	EPO; JPO;	
		and (gate adj electrode).clm. and channel.clm.	DERWENT;	
157	499		IBM_TDB	2004/44/00
157	433	(gate adj electrode) same (gate adj wiring)	USPAT;	2004/11/08
		same channel	US-PGPUB;	14:53
			EPO; JPO;	
			DERWENT;	
158	43	((aste edi electrode) some (mete edi edili e)	IBM_TDB	2004/44/20
150	43	((gate adj electrode) same (gate adj wiring)	USPAT;	2004/11/08
	:	same channel).clm.	US-PGPUB;	14:53
·			EPO; JPO;	
			DERWENT;	
150	_	(Impto adi alcatuada) assas 1 a f. 12 12 13	IBM_TDB	0004/64/00
159	1	((gate adj electrode) same (gate adj wiring)	USPAT;	2004/11/08
		same channel).clm. and (outside near10	US-PGPUB;	14:55
		channel).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
160	22	((gate adj electrode) same (gate adj wiring)	USPAT;	2004/11/08
		same channel).clm. and ((gate adj wiring)	US-PGPUB;	14:55
		near10 (conductive or conducting or	EPO; JPO;	
		material)).clm.	DERWENT;	
			IBM_TDB	

161	15	((gate adj electrode) same (gate adj wiring)	USPAT;	2004/11/08
		same channel).clm. and ((gate adj wiring)	US-PGPUB;	14:56
		near10 (conductive or conducting or	EPO; JPO;	
		material)).clm. and (channel near2	DERWENT;	
		region).clm.	IBM_TDB	
162	9	((gate adj electrode) same (gate adj wiring)	USPAT;	2004/11/08
		same (channel near2 region)).clm. and	US-PGPUB;	14:56
		((gate adj wiring) near10 (conductive or	EPO; JPO;	
	1	conducting or material)).clm. and (channel	DERWENT;	
		near2 region).clm.	IBM_TDB	
163	9	((gate adj electrode) same (gate adj wiring)	USPAT;	2004/11/08
		same (channel near2 region)).clm. and	US-PGPUB;	14:59
		((gate adj wiring) near10 (conductive or	EPO; JPO;	
		conducting or material)).clm.	DERWENT;	
		,	IBM_TDB	
164	59	(gate adj electrode) near10 (gate adj	USPAT;	2004/11/08
		wiring) near10 (different adj material)	US-PGPUB;	15:00
		willing, near to (amoront au) material,	EPO; JPO;	10.00
•			DERWENT;	
			IBM_TDB	
165	0	((gate adj electrode) near10 (gate adj	USPAT;	2004/11/08
100		wiring) near10 (different adj material)).clm.	US-PGPUB;	15:01
•		witing) hear to (different au) material)).cim.	EPO; JPO;	15:01
		· · · · · · · · · · · · · · · · · · ·	DERWENT;	
			IBM_TDB	
166	59	((gate adj electrode) near10 (gate adj	USPAT;	2004/11/08
100	33	wiring) near10 (different adj material))	i *	
		willing) hear to (unietent auj material))	US-PGPUB; EPO; JPO;	15:02
			DERWENT;	
			IBM_TDB	
167	10	((goto odi electrode) menuto (goto odi	_	2004/44/00
107	"	((gate adj electrode) near10 (gate adj wiring) near10 (different)).clm.	USPAT;	2004/11/08
		witing) hear to (different)).cim.	US-PGPUB;	15:03
			EPO; JPO;	,
		•	DERWENT;	
168	5	(mate adi alcotrodo) alm and (mate adi	IBM_TDB	0004/44/00
100	3	(gate adj electrode).clm. and (gate adj	USPAT;	2004/11/08
		wiring).clm. and (different adj	US-PGPUB;	15:0 <u>5</u>
		material).clm.	EPO; JPO;	
			DERWENT;	
400	000		IBM_TDB	
169	226	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm.	US-PGPUB;	15:06
			EPO; JPO;	
			DERWENT;	
470		(IBM_TDB	
170	69	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm. and (channel near2	US-PGPUB;	15:06
		region).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

171	10	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm. and (channel near2	US-PGPUB;	15:07
		region).clm. and (first adj (conductive or	EPO; JPO;	
		conducting) adj layer).clm.	DERWENT;	
		3 , 3 ,	IBM_TDB	
172	0	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm. and (channel near2	US-PGPUB;	15:07
		region).clm. and (first adj (conductive or	EPO; JPO;	
		conducting) adj layer).clm. and (second adj	DERWENT;	
		(conductive adj conducting) adj layer).clm.	IBM_TDB	
173	0	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm. and (channel).clm. and (first	US-PGPUB;	15:07
		adj (conductive or conducting) adj	EPO; JPO;	10.0.
		layer).clm. and (second adj (conductive adj	DERWENT;	
		conducting) adj layer).clm.	IBM_TDB	
174	25	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
•••		electrode).clm. and (channel).clm. and	US-PGPUB;	15:09
		((conductive or conducting) adj layer).clm.	EPO; JPO;	13.03
		((conductive of conducting) adjuger,.ciiii.	DERWENT;	
		,	IBM_TDB	'
175	25	(gate adj wiring).clm. and (gate adj	_	2004/44/09
175	25	electrode).clm. and (channel).clm. and	USPAT;	2004/11/08
		((conductive or conducting) adj layer).clm.	US-PGPUB;	15:09
		and channel.clm.	EPO; JPO;	
		and Channel.Cim.	DERWENT;	
176	40	(acts adingina) also and (acts adi	IBM_TDB	0004/44/00
176	19	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm. and (channel).clm. and ((conductive or conducting) adj layer).clm.	US-PGPUB;	15:10
		and (channel near2 region).clm.	EPO; JPO;	
		and (Channel hear2 region).Clm.	DERWENT;	
177	5	(goto odi wiring) olum and (goto odi	IBM_TDB	2004/44/09
'''		(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm. and (channel).clm. and	US-PGPUB;	15:14
		((conductive or conducting) adj layer).clm.	EPO; JPO;	
		and (channel near2 region).clm. and (wiring	DERWENT;	
178	4	near10 channel).clm.	IBM_TDB	0004/44/00
176	4	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm. and (channel).clm. and	US-PGPUB;	15:14
		((conductive or conducting) adj layer).clm.	EPO; JPO;	
		and (channel near2 region).clm. and (wiring	DERWENT;	
		near10 channel).clm. and (first adj	IBM_TDB	
470	ا ۾ ا	(conducting or conductive) adj layer).clm.		00044455
179	4	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm. and (channel).clm. and	US-PGPUB;	15:18
		((conductive or conducting) adj layer).clm.	EPO; JPO;	
		and (channel near2 region).clm. and (wiring	DERWENT;	,
		near10 channel).clm. and (first adj	IBM_TDB	,
		(conducting or conductive) adj layer).clm.		
		and (second adj (conducting or conductive)		
		adj layer).clm.		

180	4	(gate adj wiring).clm. and (gate adj	USPAT;	2004/11/08
		electrode).clm. and (channel).clm. and	US-PGPUB;	15:18
		((conductive or conducting) adj layer).clm.	EPO; JPO;	
		and (channel near2 region).clm. and (wiring	DERWENT;	
		near10 channel).clm. and (first adj	IBM_TDB	•
		(conducting or conductive) adj layer).clm.	,	·
		and (second adj (conducting or conductive)		
		adj layer).clm. and (channel near10		
		wiring).clm.		